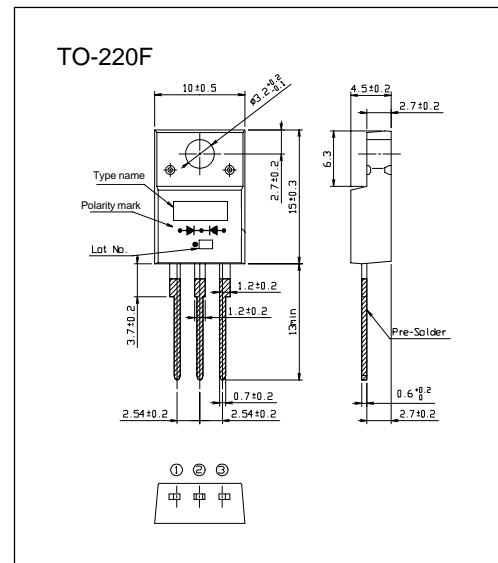


SCHOTTKY BARRIER DIODE

Outline drawings, mm



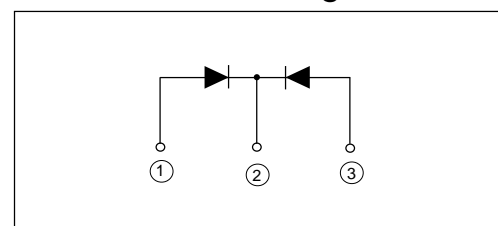
Features

- Low V_F
- Super high speed switching
- High reliability by planer design

Applications

- High speed power switching

Connection diagram



Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}		30	V
Repetitive peak surgereverse voltage	V_{RSM}	$t_w=500ns$, $duty=1/40$	35	V
Average output current	I_o	Square wave, $duty=1/2$ $T_c=85^\circ C$	38*	A
Surge current	I_{FSM}	Sine wave 10ms	200	A
Operating junction temperature	T_j		-40 to +150	$^\circ C$
Storage temperature	T_{stg}		-40 to +150	$^\circ C$

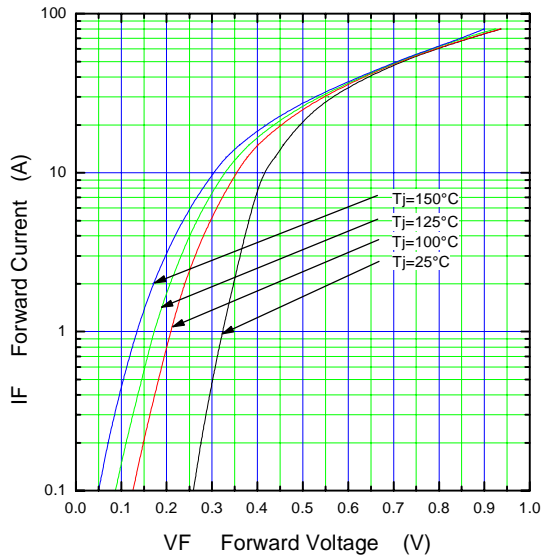
* Average forward current of centertap full wave connection

- Electrical characteristics ($T_a=25^\circ C$ Unless otherwise specified)

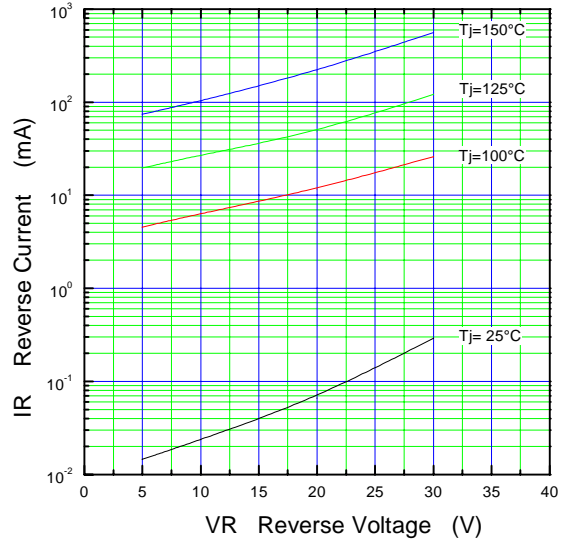
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	$I_{FM}=12.5A$	0.45	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	10	mA
Thermal resistance	$R_{th(j-c)}$	Junction to case	2.0	$^\circ C/W$

■ Characteristics

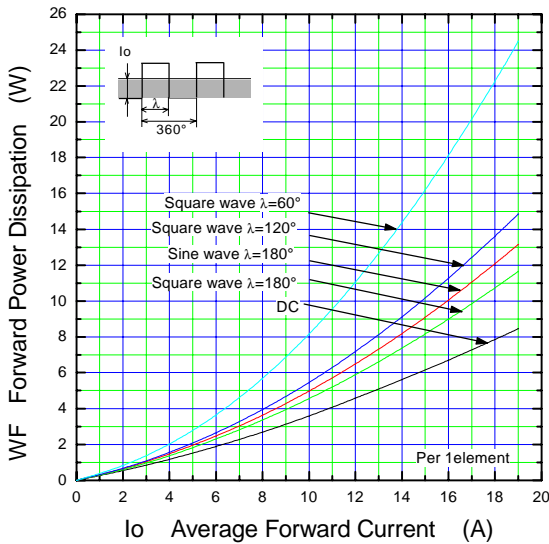
Forward Characteristic (typ.)



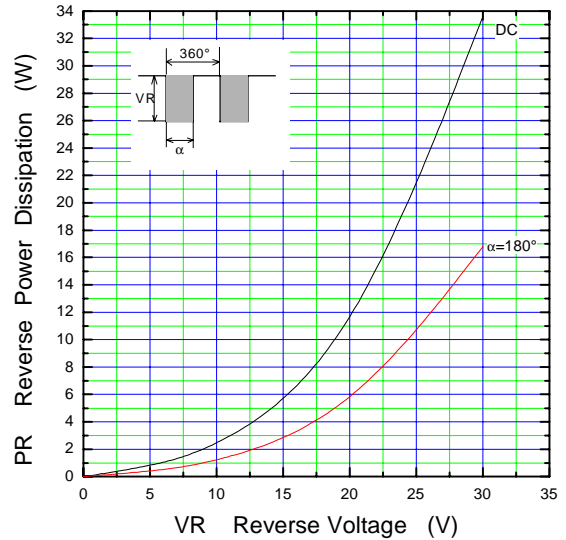
Reverse Characteristic (typ.)



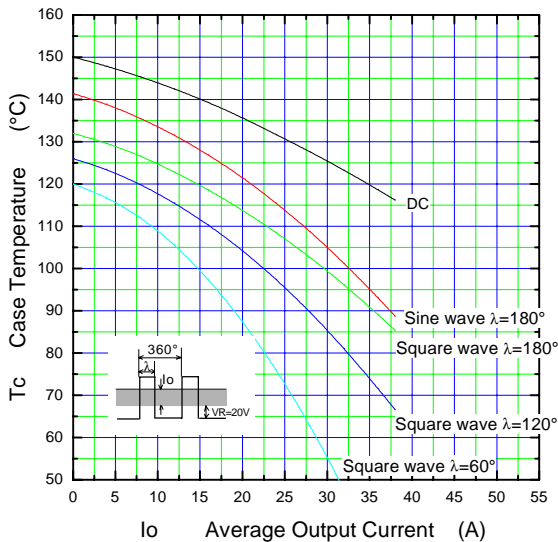
Forward Power Dissipation



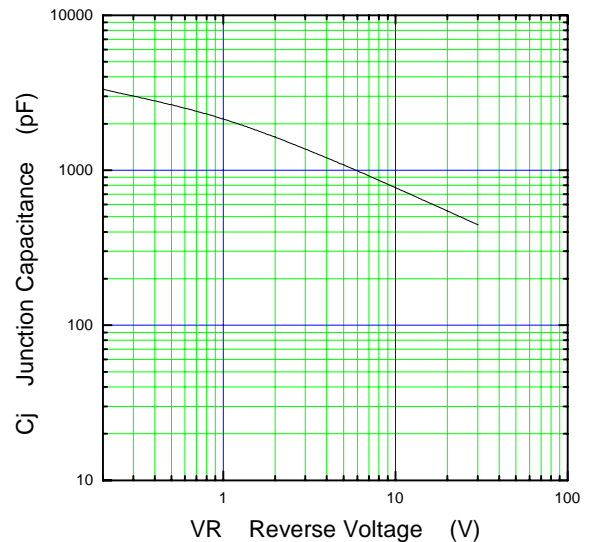
Reverse Power Dissipation



Current Derating (Io-Tc)



Junction Capacitance Characteristic (typ.)



f: Conduction angle of forward current for each rectifier element
Io: Output current of center-tap full wave connection

